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H01L 21/3213**G03F 7/32****H01L 21/027****H01L 21/3205****// H01L 29/786**(21) Application number: **05176101**(71) Applicant: **CASIO COMPUT CO LTD**(22) Date of filing: **22.06.93**(72) Inventor: **NAITO HIDEO**(54) **METHOD OF PATTERNING ALUMINUM SYSTEM METAL FILM**

apparatus as one process.

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(57) Abstract:

PURPOSE: To reduce the number of processes, improve the yield and improve the throughput when the aluminum system metal film of a semiconductor device is patterned into a required pattern.

CONSTITUTION: A photoresist layer 3 is applied to an aluminum film 2 formed on the upper surface of an insulating substrate 1 and the photoresist layer 3 is exposed so as to have a required pattern with a glass mask 4. While the exposed photoresist layer 3 is developed by developer (TMAH) containing 1ppm 1000ppm of chlorine ions, the foundation side aluminum film 2 is etched by the developer. As the TMAH developer functions not only as the developer of the photoresist layer 3 but also as the etchant of the aluminum film 2, the development process of the photoresist layer and the etching process using the photoresist layer can be performed in a same

